



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cabral, Jr. et al.

Serial No.: 09/902,483

Group Art Unit: 2813

Filed: July 11, 2001

Examiner: Bowers, C.

For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY
CONTACTS TO THIN FILM SILICIDE-ON-INSULATOR AND BULK MOSFETS
AND FOR SHALLOW JUNCTIONS

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

**RESPONSE TO FIRST OFFICE ACTION AND RESTRICTION
REQUIREMENT**

Sir:

In response to the Office Action dated December 27, 2001, please consider the following:

REMARKS

In response to the Examiner's restriction requirement, Applicant hereby elects the invention of Group I (e.g., the semiconductor device as defined by claims 1-13), without traverse. Applicant reserves the opportunity to file a Divisional Application for the non-elected invention later.

Early, favorable prosecution on the merits is respectfully requested.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

#8
1/23/02
Harrison
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JAN 16 2002
TECHNOLOGY CENTER 2800